## IN THE SPECIFICATION:

Please amend the paragraph beginning at page 7, line 9, and ending at page 7, line 11, as follows:

--Fig. 11 is a graph showing the spectral transmittance characteristics of an infrared ray cut filer filter.--

Please amend the paragraph beginning at page 13, line 17, and ending at page 14, line 10, as follows:

--The semiconductor chip 503 will be described in more detail with reference to Figs. 1B and 1C. As shown in Fig. 1B, between the compound eye optical element 512 and compound eye optical system 503, the spacer 522 made of resin, glass, silicon or the like is disposed in order to hold them at a predetermined distance. The spacer 522 and semiconductor chip 503 may be bonded together by utilizing a bonding process to be used when a silicon on insulator (SIO) (SOI) substrate is formed. It is preferable to bond them together by using adhesive metal which contains aluminum or indium. The convex lenses 600a, 600b, 600c and 600d are formed on the light transmissive member 501 by a replica method, an injection molding method, a compression molding method or the like. The convex lens 600a - 600d is a spherical surface Fresnel convex lens or a circular, axis-symmetrical, non-spherical surface Fresnel convex lens, respectively made of resin with which a curved image surface can be corrected more reliably as compared to a usual optical system using a continuous image surface.

Please amend the paragraph beginning at page 14, line 24, and ending at page 15, line 17, as follows:

along the optical axis direction determines a main light beam outside the optical axis of the optical system. Therefore, the stop position is very important from the viewpoint of controlling various aberrations. Since each convex lens 600a - 600d is formed on the image side, various optical aberrations can be corrected properly if the stop is positioned near at the center of a spherical surface approximating a Fresnel lens surface. If a color image is desired to be picked up, a green (G) transmissive filter, a red (R) transmissive filter and a blue (B) transmissive filter are disposed, for example, in a Bayer layout, near at each convex lens 600a - 600d along the optical axis. If a particular color image or an X-ray image is desired to be picked up, the particular color filter or phosphor is disposed. In this embodiment, although not shown, a green (G) transmissive filter filter, a red (R) transmissive filter and a blue (B) transmissive filter are disposed in a Bayer layout.--

Please amend the paragraph beginning at page 18, line 9, and ending at page 18, line 17, as follows:

--By properly selecting the eccentricity amounts of the micro lenses 516a and 516b, only a desired light flux becomes incident upon each light reception element 822. The eccentricity amounts can be set so that a subject light beam passed through the stop aperture 810a is received mainly in the light reception area 820a, a subject light beam passed through the stop aperture 810b is received mainly in the light reception area 820b, etc.--

Please amend the paragraph beginning at page 26, line 20, and ending at page 26, line 25, as follows:

--The infrared ray cut filter 560 is formed in the peripheral area of the stop light shielding when the spectral transmittance of the infrared ray cut filter in this area is regulated to transmit ultraviolet rays, the epoxyresin epoxy resin can be hardened by ultraviolet ray radiation from a front of the semiconductor wafer 910.--

Please amend the paragraph beginning at page 29, line 1, and ending at page 29, line 10, as follows:

--In the above embodiment, two spacers are used for the spacer 901 and two compound eye optical elements are used as the optical element set 917. Three or four spacers and compound eye optical elements may also be used. In order to reduce the number of position alignment processes, the spacer 901 and the like may has have the size-similar to the semiconductor wafer 910, and the openings 902 and convex lenses 600 are formed at positions corresponding to each semiconductor chip 503 on the semiconductor wafer 910.--